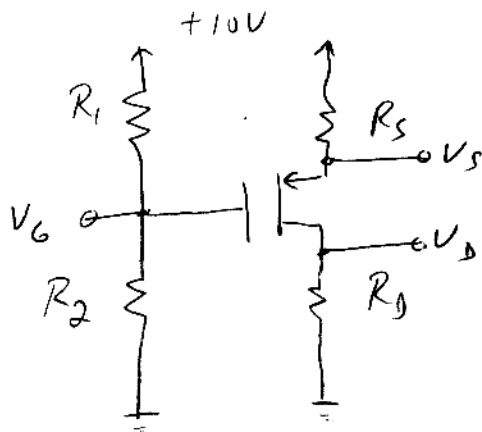


EE 321
Fall 2002

Homework #13

Solutions

5.63 (a)



Want $10 \mu A$ through

$R_1 + R_2$, so

$$R_1 + R_2 = \frac{10V}{10 \mu A} = 1 M\Omega$$

$$k_p' \frac{W}{L} = 0.5 mA/V^2$$

$$V_t = -1V$$

Want $I_D = 1 mA$

$$V_D = 3V$$

$$V_D = I_D R_D \quad R_D = \frac{V_D}{I_D} = \frac{3V}{1mA} = 3 k\Omega$$

$$I_D = \frac{1}{2} k_p' \frac{W}{L} (V_{GS} - V_t)^2$$

$$k_p' \frac{W}{L} = 0.5 mA/V^2 \quad V_t = -1V$$

$$1mA = \frac{1}{2} (0.5 mA/V^2) (V_{GS} - (-1V))^2$$

$$4V^2 = (V_{GS} + 1V)^2$$

$$V_{GS} = -3V \text{ or } +1V$$

For PMOS need $V_{GS} < V_t$, so $V_{GS} = -3V$

$$\text{At triode, } V_{DS} = V_{GS} - V_t = -3V - (-1V) = -2V$$

To be $1V$ above triode, need $V_{DS} = -3V$

$$V_S = V_D - V_{DS} = 3V - (-3V) = 6V$$

$$V_G = V_{GS} + V_S = -3V + 6V = 3V$$

$$V_G = \frac{R_2}{R_1 + R_2} V_{DD} \Rightarrow R_2 = \frac{V_G}{V_{DD}} (R_1 + R_2) = \frac{3V}{10V} 1M\Omega = 300k\Omega$$

$$V_S = V_{DD} - I_D R_S \Rightarrow R_S = \frac{V_{DD} - V_S}{I_D} = \frac{10V - 6V}{1mA} = 4k\Omega$$

$$\therefore R_1 = 300k \quad R_S = 4k\Omega$$

$$R_2 = 700k \quad R_D = 3k\Omega$$

(b) As in (a) $R_1 + R_2 = 10 \text{ k}\Omega$ $R_D = 3 \text{ k}\Omega$

$$I_D = \frac{1}{2} k_p' \frac{W}{L} (V_{GS} - V_{t'})^2$$

$$|V_{t'}| = 2 \text{ V} \Rightarrow V_{t'} = +2 \text{ V} \quad (\text{Depletion P-MOS})$$

$$k_p' \frac{W}{L} = 0.5 \text{ mA/V}^2$$

$$1 \text{ mA} = \frac{1}{2} (0.5 \text{ mA/V}^2) (V_{GS} - 2 \text{ V})^2$$

$$4 \text{ V}^2 = (V_{GS} - 2 \text{ V})^2$$

$$V_{GS} = 0 \text{ V, } 4 \text{ V} \quad \text{Need } V_{GS} < V_{t'}, \text{ so } V_{GS} = 0 \text{ V}$$

$$\text{At triode, } V_{DS} = V_{GS} - V_{t'} = 0 - 2 \text{ V} = -2 \text{ V}$$

$$\text{To be } 1 \text{ V above triode need } V_{DS} = -3 \text{ V}$$

$$V_S = V_D - V_{DS} = 3 \text{ V} - (-3 \text{ V}) = 6 \text{ V}$$

$$V_S = I_{DD} R_S \Rightarrow R_S = \frac{V_{DD} - V_S}{I_D} = 4 \text{ k}\Omega$$

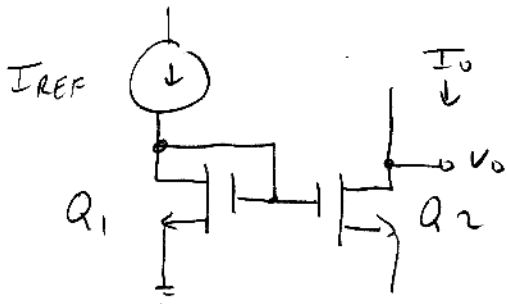
$$V_G = V_{GS} + V_S = 0 + 6 \text{ V} = 6 \text{ V}$$

$$V_G = \frac{R_2}{R_1 + R_2} V_{DD} \Rightarrow R_2 = \frac{V_G}{V_{DD}} (R_1 + R_2) = 600 \text{ k}\Omega$$

$$\therefore R_1 = 400 \text{ k}\Omega \quad R_S = 4 \text{ k}\Omega$$

$$R_2 = 600 \text{ k}\Omega \quad R_D = 3 \text{ k}\Omega$$

5.71



$$k_n' \frac{W}{L} = 40 \mu\text{A/V}^2$$

$$V_t = 0.8 \text{ V}$$

$$V_A = 20 \text{ V}$$

$$I_{REF} = 10 \mu\text{A}$$

$$I_{D1} = \frac{1}{2} k_n' \frac{W}{L} (V_{GS} - V_t)^2 = I_{REF}$$

$$10 \mu\text{A} = \frac{1}{2} (40 \mu\text{A/V}^2) (V_{GS} - 0.8 \text{ V})^2$$

$$\frac{1}{2} \text{ V}^2 = (V_{GS} - 0.8 \text{ V})^2$$

$$V_{GS} = 0.8 \text{ V} \pm \sqrt{\frac{1}{2} \text{ V}^2} = 1.51 \text{ V}, -0.93 \text{ V}$$

$$\text{Need } V_{GS} > V_t \text{ so } V_{GS} = 1.51 \text{ V}$$

$$\text{For } I_o = I_{REF} \text{ need } V_{DS2} = V_{DS1}$$

$$V_{D2} = V_{G2} \text{ so } V_{DS2} = 1.51 \text{ V} \Rightarrow V_{DS2} = 1.51 \text{ V} \Rightarrow V_{D2} = 1.51 \text{ V}$$

$$V_o = V_{D2} = 1.51 \text{ V}$$

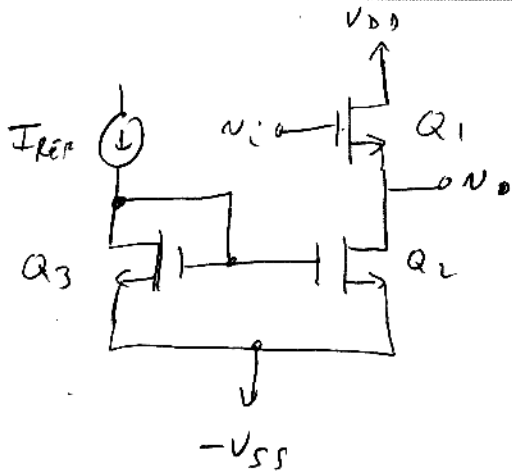
$$r_{o2} = \frac{V_A}{I_D} = \frac{20 \text{ V}}{10 \mu\text{A}} = 2 \text{ M}\Omega$$

$$\Delta V_{DS} = r_o \Delta i_D$$

$$\Delta i_D = \frac{\Delta V_{DS}}{r_o} = \frac{2 \text{ V}}{2 \text{ M}\Omega} = 1 \mu\text{A}$$

I_o is $11 \mu\text{A}$ when V_{DS} increases by 2 V

5.80



$$k_n' = 20 \mu\text{A}/\text{V}^2$$

$$V_E = 1\text{V}$$

$$V_A = 100\text{V}$$

$$\frac{W}{L} = 10$$

$$I_{REF} = 200 \mu\text{A}$$

$$\chi = 0.1$$

Because the transistors are identical,
 $I_{D2} = I_{D3} = 200 \mu\text{A}$

$$I_{D1} = I_{D2} = 200 \mu\text{A}$$

$$g_{m1} = \sqrt{2k_n'} \sqrt{\frac{W}{L}} \sqrt{I_{D1}} = \sqrt{2(20 \mu\text{A}/\text{V}^2)(10)(200 \mu\text{A})}$$

$$= 0.28 \text{ mA/V}$$

$$r_{o1} = r_{o2} = \frac{V_A}{I_D} = \frac{100\text{V}}{200 \mu\text{A}} = 500 \text{ k}\Omega$$

eqn
5.70

$$A_v = \frac{g_{m1}}{g_{m1} + g_{m_{b1}} + \frac{1}{r_{o1}} + \frac{1}{r_{o2}}} = \frac{g_{m1}}{g_{m1}(1+\chi) + \frac{1}{r_{o1}} + \frac{1}{r_{o2}}}$$

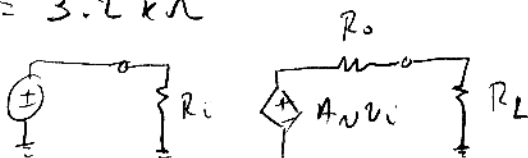
$$= \frac{0.28 \text{ mA/V}}{0.28 \text{ mA/V}(1+0.1) + \frac{1}{500 \text{ k}} + \frac{1}{500 \text{ k}}}$$

$$= 0.90 \text{ V/V}$$

eqn
5.73

$$R_o = \left(\frac{1}{g_{m1}} \right) \parallel \left(\frac{1}{g_{m_{b1}}} \right) \parallel r_{o1} \parallel r_{o2} = \frac{1}{g_{m1} + g_{m_{b1}} + \frac{1}{r_{o1}} + \frac{1}{r_{o2}}}$$

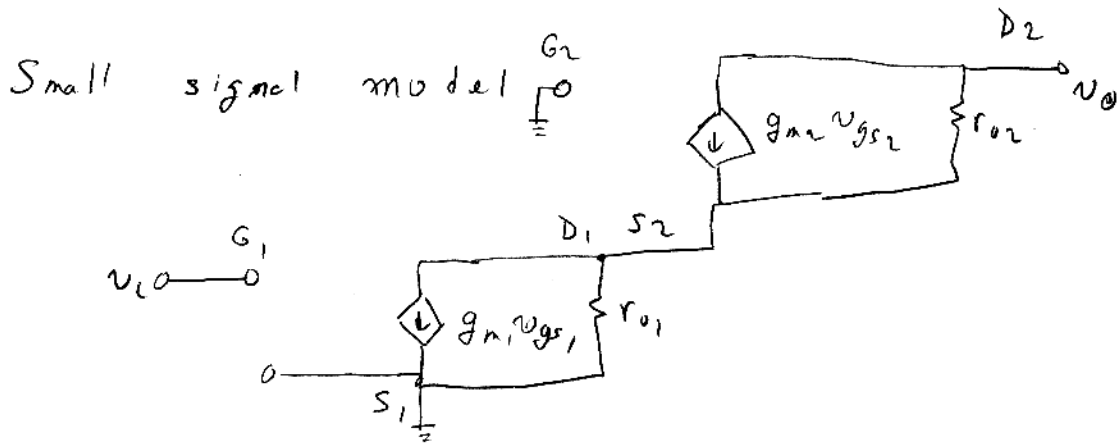
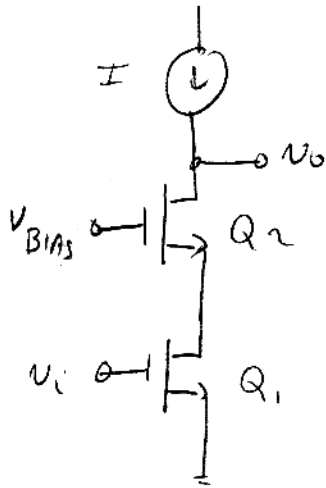
$$= 3.2 \text{ k}\Omega$$



$$A_{v_{new}} = \frac{R_L}{R_L + R_o} A_v = \frac{10 \text{ k}}{10 \text{ k} + 3.2 \text{ k}} \cdot 0.9 \text{ V/V}$$

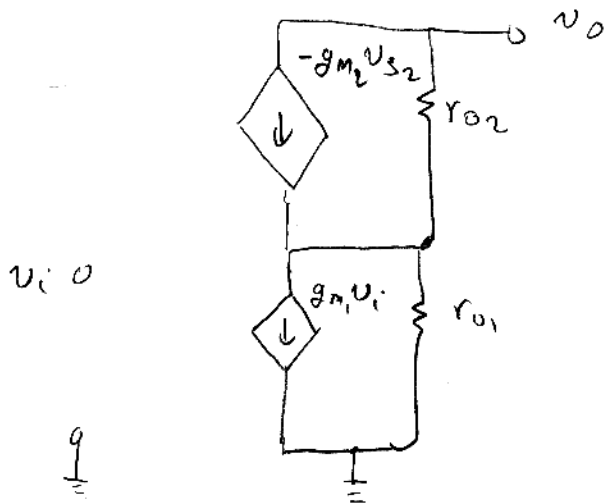
$$= 0.68 \text{ V/V}$$

5.81

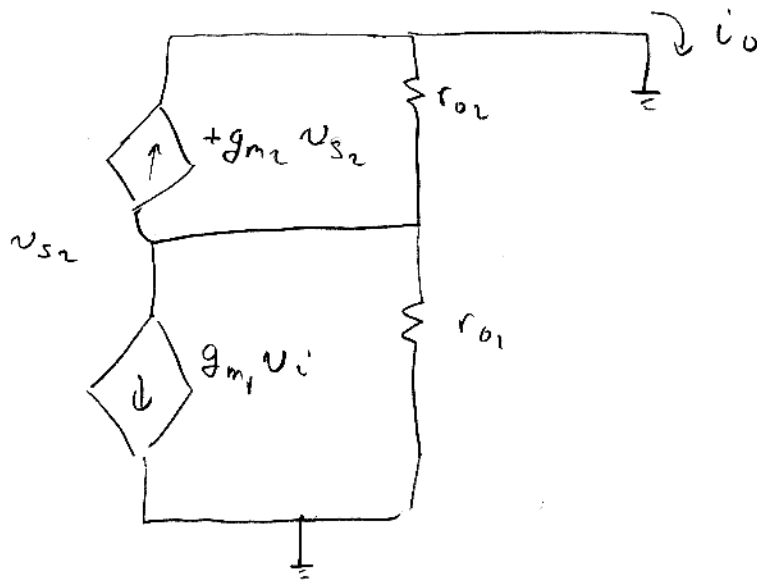


$$v_{gs1} = v_i \quad v_{gs2} = -v_{s2}$$

Redraw



(a) Find short-circuit output current



Node eqn at S_2 :

$$g_{m1} v_i + g_{m2} v_{s2} + \frac{v_{s2}}{r_{o1}} + \frac{v_{s2}}{r_{o2}} = 0$$

$$v_{s2} = \frac{-g_{m1}}{g_{m2} + \frac{1}{r_{o1}} + \frac{1}{r_{o2}}} v_i$$

$$i_o = g_{m2} v_{s2} + \frac{v_{s2}}{r_{o2}}$$

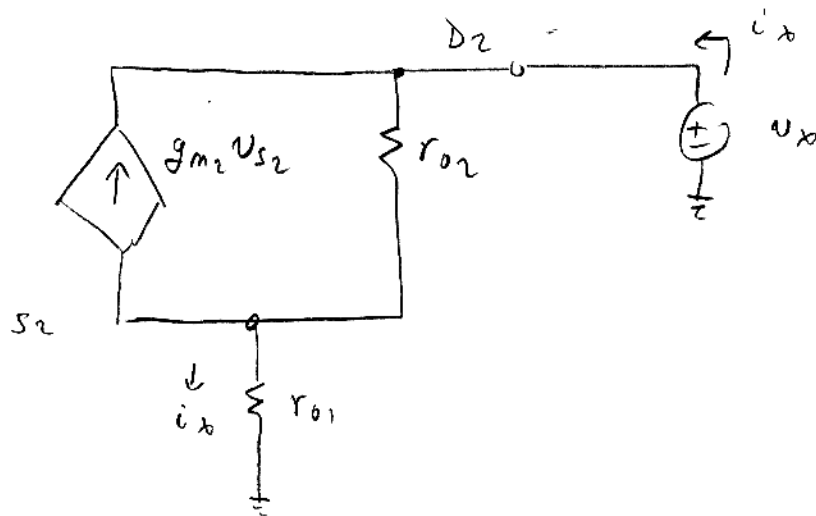
$$= \frac{-g_{m1} \left(g_{m2} + \frac{1}{r_{o2}} \right)}{g_{m2} + \frac{1}{r_{o1}} + \frac{1}{r_{o2}}} v_i$$

$$\approx -g_{m1} v_i \quad (\text{for large } r_{o1}, r_{o2})$$

$$\frac{i_o}{v_i} \approx -g_{m1}$$

(b) With v_i shorted, $v_i = 0 \Rightarrow g_m v_i = 0$

Model becomes



Node eqn at D_2 :

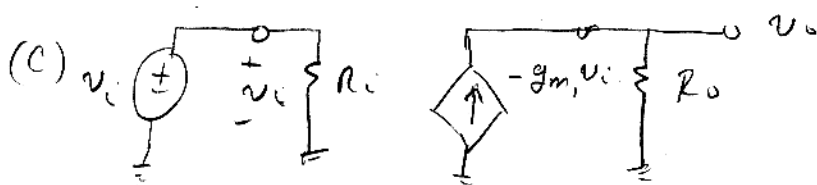
$$i_x + g_{m2} v_{s2} + \frac{v_{s2} - v_x}{r_{o2}} = 0$$

Also, $v_{s2} = i_x r_{o1}$, so

$$i_x + g_{m2} i_x r_{o1} + \frac{i_x r_{o1} - v_x}{r_{o2}} = 0$$

$$i_x \left(1 + g_{m2} r_{o1} + \frac{r_{o1}}{r_{o2}} \right) = \frac{v_x}{r_{o2}}$$

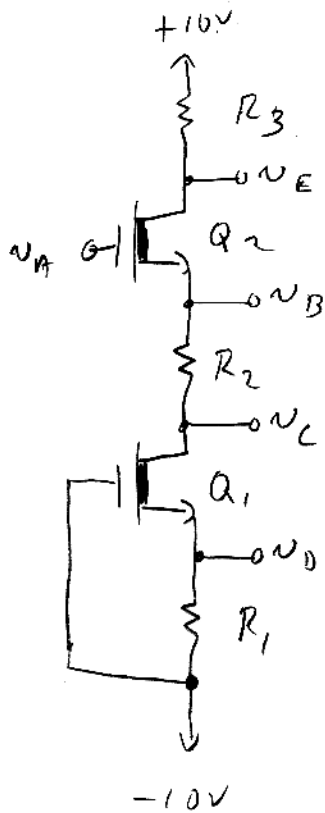
$$R_o = \frac{v_x}{i_x} = r_{o1} + r_{o2} + g_{m2} r_{o1} r_{o2} \approx g_{m2} r_{o1} r_{o2}$$



$$v_o = -g_{m1} R_o v_i \approx -g_{m1} g_{m2} r_{o1} r_{o2} v_i$$

$$A_{v0} \approx -g_{m1} g_{m2} r_{o1} r_{o2}$$

5.84



$$I_{DSS} = 4 \text{ mA}$$

$$|V_t| = 2 \text{ V} \Rightarrow V_t = -2 \text{ V} \text{ (Depletion NMOS)}$$

$$I_{DSS} = \frac{1}{2} k_n' \frac{W}{L} V_t^2$$

$$k_n' \frac{W}{L} = \frac{2 I_{DSS}}{V_t^2} = \frac{2(4 \text{ mA})}{(-2 \text{ V})^2} = 2 \text{ mA/V}^2$$

$$I_{D1} = \frac{1}{2} k_n' \left(\frac{W}{L}\right) (V_{GS1} - V_t)^2$$

$$1 \text{ mA} = \frac{1}{2} (2 \text{ mA/V}^2) (V_{GS1} - (-2 \text{ V}))^2$$

$$1 \text{ V}^2 = (V_{GS1} + 2 \text{ V})^2$$

$$V_{GS1} = -1 \text{ V} \text{ or } -3 \text{ V}$$

$$\text{Need } V_{GS1} > V_t, \text{ so } V_{GS1} = -1 \text{ V}$$

\therefore 1V drop across R_1

$$R_1 = \frac{V_1}{I_D} = \frac{1 \text{ V}}{1 \text{ mA}} = 1 \text{ k}\Omega$$

$$R_2 = R_1 = 1 \text{ k}\Omega$$

$$V_E = V_{DD} - R_3 I_D \Rightarrow R_3 = \frac{10 \text{ V} - 6 \text{ V}}{1 \text{ mA}} = 4 \text{ k}\Omega$$

Because the transistors are equal, and have equal I_D ,

$$V_{GS2} = V_{GS1} = -1 \text{ V}$$

$$V_{GS2} = V_{G2} - V_{S2} = V_A - V_{S2} \Rightarrow V_{S2} = V_A - V_{GS2} = 0 - (-1) = 1 \text{ V}$$

$$V_B = V_{S2} = 1 \text{ V}$$

$$V_C = V_B - R_2 I_D = 1 \text{ V} - (1 \text{ k}\Omega)(1 \text{ mA}) = 0 \text{ V}$$

Note that $v_{s2} = v_A - v_{gs2} = v_A + 1V$, $v_B = v_{s2} = v_A + 1V$

$$v_c = v_B - I_D R_1 = v_A + 1V - (1mA)(1k\Omega) = v_A$$

$v_c = v_A$ as long as both transistors remain in saturation

Q_2 enters triode when

$$v_{DS2} = v_{GS2} - V_t = -1V - (-2V) = 1V$$

$$v_{D2} = v_E = 6V$$

$$\begin{aligned} v_A = v_{S2} + v_{GS2} &= v_{D2} - v_{DS2} + v_{GS2} \\ &= 6V - 1V - 1V = 4V \end{aligned}$$

Q_1 enters triode when

$$v_{DS1} = v_{BS1} - V_t = -1V - (-2V) = 1V$$

$$\begin{aligned} v_A = v_{Dc} = v_{D1} &= v_{DS1} + v_{S1} = v_{DS1} + I_D R_1 - 10V \\ &= 1V + (1mA)(1k\Omega) - 10V \\ &= -8V \end{aligned}$$

Circuit works as a follower with unity gain and no offset for $-8V < v_A < 4V$